ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE128P (NPN) & NTE129P (PNP)
Silicon Complementary Transistors
General Purpose Amp

Description:

The NTE128P (NPN) and NTE129P (PNP) are silicon complemedntary transistors designed for use in general purpose power amplifier and switching applications.

Features:

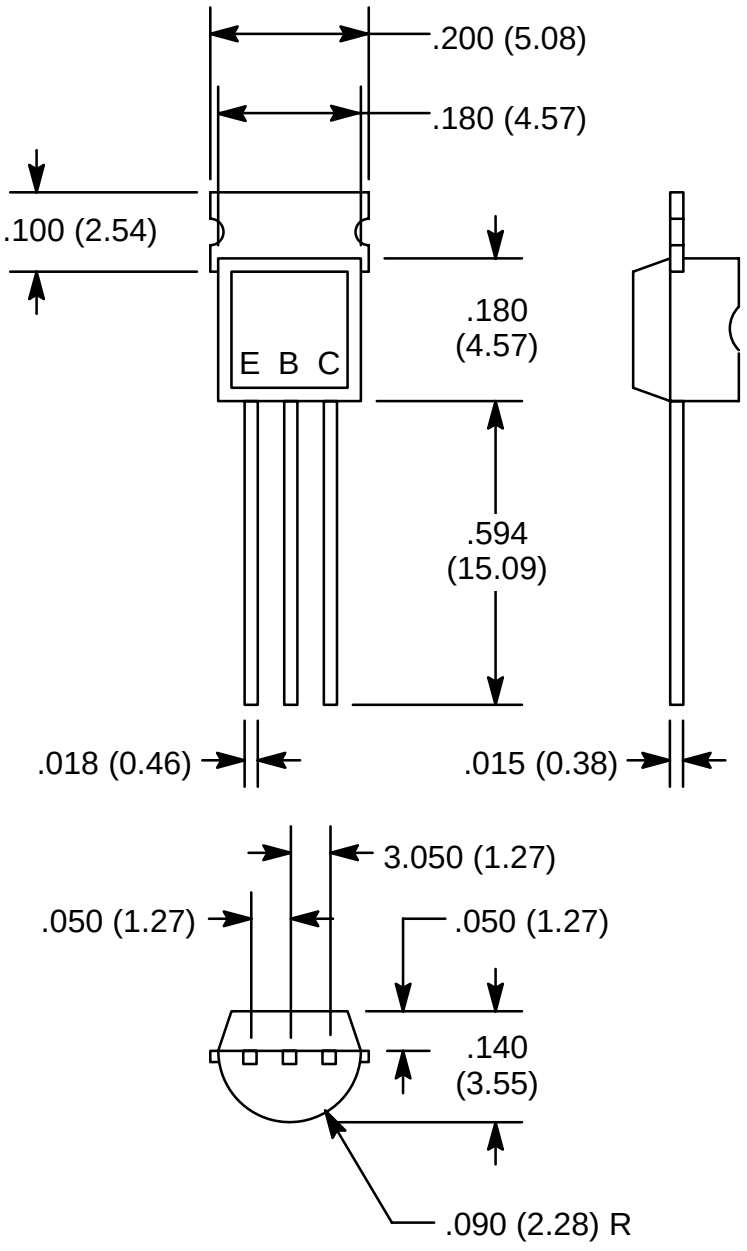
- High V_{CE} Ratings
- Exceptional Power Dissipation Capability

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 100V
Collector–Emitter Voltage, V_{CEO} 80V
Emitter–Base Voltage, V_{EBO} 5V
Continuous Collector Current , I_C 1A
Power Dissipation, P_{TOT}
T_A = +25°C 0.850W
T_C = +25°C 2W
Operating Junction Temperature Range, T_J . . . . . –55° to +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C
Thermal Resistance, Junction–to–Ambient, R_{thJA} . . . . . 147°C/W
Thermal Resistance, Junction–to–Case, R_{thJC} . . . . . 62.5°C/W

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage	BV_{CEO}	I_C = 10mA, I_B = 0	80	–	–	V
Collector Cutoff Current	I_{CBO}	V_{CB} = 80V	–	–	100	nA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V	–	–	100	nA
DC Current Gain	h_{FE}	I_C = 10mA, V_{CE} = 2V	100	–	–	
		I_C = 350mA, V_{CE} = 2V	100	–	300	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 350mA	–	–	0.35	V
Current Gain Bandwidth Product	f_T	I_C = 50mA	50	–	–	
Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	–	–	15	pF


.200 (5.08)
.180 (4.57)
.100 (2.54)
.180
(4.57)
E B C
.594
(15.09)
.018 (0.46)
.015 (0.38)
3.050 (1.27)
.050 (1.27)
.050 (1.27)
.140
(3.55)
.090 (2.28) R